



Fast, Low-Voltage, Dual 4Ω SPDT CMOS Analog Switches

MAX4635/MAX4636

General Description

The MAX4635/MAX4636 are fast, dual 4Ω single-pole/double-throw (SPDT) analog switches that operate with supply voltages from +1.8V to +5.5V. High switching speeds, 1Ω on-resistance flatness, and low power consumption make these devices ideal for audio/video, communications, and battery-operated devices. Containing two independently controllable SPDT switches in 10-pin μMAX and 10-pin 3mm x 3mm thin QFN packages, the MAX4635/MAX4636 use little board space, and have low power consumption ensuring minimal impact on your power budget. The analog signal range extends to the supply rails. The MAX4635 has inverted logic compared to the MAX4636.

Applications

- Battery-Powered Equipment
- Relay Replacement
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- Sample-and-Hold Circuits
- Communications Circuits

Features

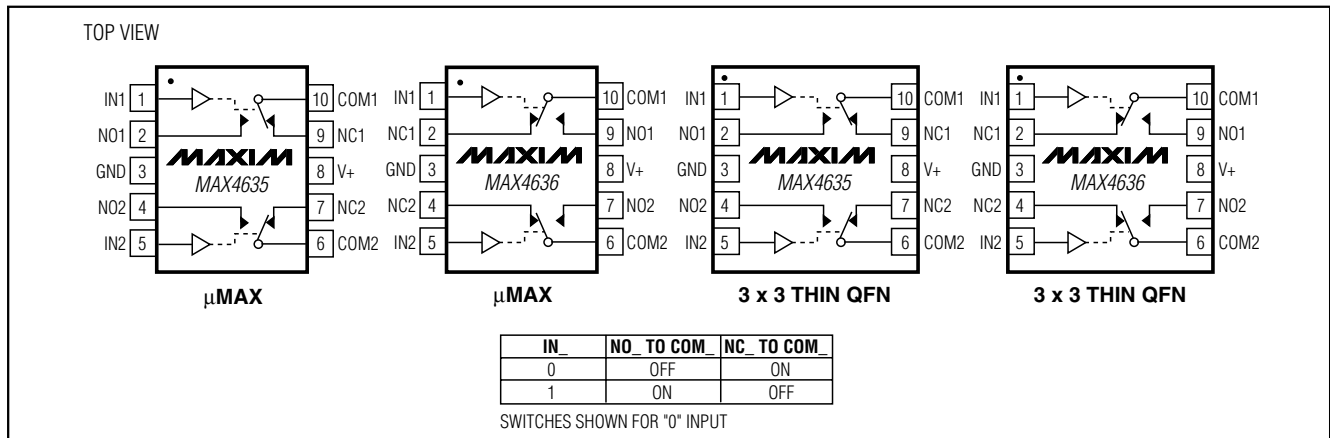
- ◆ **Guaranteed On-Resistance**
4Ω (max) +5V Supply
5.5Ω (max) +3V Supply
- ◆ **Guaranteed Match Between Channels**
0.2Ω (max)
- ◆ **Guaranteed Flatness Over Signal Range**
1Ω (max) with +5V Supply
- ◆ **Fast Switching Speeds**
14ns (max) Turn-On Time
6ns (max) Turn-Off Time
- ◆ **1.8V Operation**
100Ω (typ) On-Resistance Over Temperature
56ns (typ) Turn-On Time
17ns (typ) Turn-Off Time
- ◆ **+1.8V to +5.5V Single-Supply Operation**
- ◆ **Rail-to-Rail® Signal Handling**
- ◆ **Low Crosstalk: -67dB at 1MHz**
- ◆ **High Off-Isolation: -65dB at 1MHz**
- ◆ **THD: 0.1%**

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE	TOP MARK
MAX4635EUB	-40°C to +85°C	10 μMAX	—
MAX4635ETB	-40°C to +85°C	10 Thin QFN (3 × 3)	AAT
MAX4636EUB	-40°C to +85°C	10 μMAX	—
MAX4636ETB	-40°C to +85°C	10 Thin QFN (3 × 3)	AAO

Rail-to-Rail is a registered trademark of Nippon Motorola, Ltd.

Pin Configuration/Functional Diagram/Truth Table



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ABSOLUTE MAXIMUM RATINGS

(Voltages Referenced to GND)

V+, IN_	-0.3V to +6V
COM_, NC_, NO_ (Note 1)	-0.3V to (V+ + 0.3V)
Continuous Current into Any Terminal	±30mA
Peak Current into COM_, NC_, NO_ (pulsed at 1ms, 10% duty cycle)	±100mA

Continuous Power Dissipation (T_A = +70°C)

10-Pin μMAX (derate 4.7mW/°C above +70°C)	330mW
10-Pin Thin QFN (derate 24.4mW/°C above +70°C)	1951mW
Operating Temperature Range	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Note 1: Signals on NO_, NC_, or COM_ exceeding V+ or GND are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Single +5V Supply

(V+ = +4.5V to +5.5V, V_{IH} = +2.4V, V_{IL} = +0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 9)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
ANALOG SWITCH							
Analog Signal Range	V _{COM_} , V _{NO_} , V _{NC_}		0		V+	V	
On-Resistance	R _{ON}	V+ = 4.5V, I _{COM_} = 10mA, V _{NO_} or V _{NC_} = 0 to V+	T _A = +25°C	2.5	4	Ω	
			T _A = T _{MIN} to T _{MAX}		4.5		
On-Resistance Match Between Channels (Notes 3, 4)	ΔR _{ON}	V+ = 4.5V, I _{COM_} = 10mA, V _{NO_} or V _{NC_} = 0 to V+	T _A = +25°C	0.1	0.2	Ω	
			T _A = T _{MIN} to T _{MAX}		0.4		
On-Resistance Flatness (Note 5)	R _{FLAT(ON)}	V+ = 4.5V, I _{COM_} = 10mA, V _{NO_} or V _{NC_} = 0 to V+	T _A = +25°C	0.5	1	Ω	
			T _A = T _{MIN} to T _{MAX}		1.2		
NO_, NC_ Off-Leakage Current (Note 6)	I _{NC_(OFF)} , I _{NO_(OFF)}	V+ = 5.5V; V _{COM_} = 1V, 4.5V; V _{NO_} or V _{NC_} = 4.5V, 1V	T _A = +25°C	-0.1	±0.01	0.1	nA
			T _A = T _{MIN} to T _{MAX}	-0.3		0.3	
COM_ Off-Leakage Current (Note 6)	I _{COM_(OFF)}	V+ = 5.5V; V _{COM_} = 1V, 4.5V; V _{NO_} or V _{NC_} = 4.5V, 1V	T _A = +25°C	-0.1	±0.01	0.1	nA
			T _A = T _{MIN} to T _{MAX}	-0.3		0.3	
COM_ On-Leakage Current (Note 6)	I _{COM_(ON)}	V+ = 5.5V; V _{COM_} = 4.5V, 1V; V _{NO_} or V _{NC_} = 4.5V, 1V or floating	T _A = +25°C	-0.1	±0.01	0.1	nA
			T _A = T _{MIN} to T _{MAX}	-0.3		0.3	
DIGITAL I/O (IN1, IN2)							
Input Logic High	V _{IH}		2.4			V	
Input Logic Low	V _{IL}				0.8	V	
Input Leakage Current	I _{IH} , I _{IL}	V _{IN_} = 0 or +5.5V	-100	5	100	nA	

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ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)

(V+ = +4.5V to +5.5V, VIH = +2.4V, VIL = +0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at TA = +25°C.) (Notes 2, 9)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DYNAMIC						
Turn-On Time (Note 6)	tON	VNO_, VNC_ = 3V; RL = 300Ω, CL = 35pF, Figure 1a	TA = +25°C	12	14	ns
			TA = TMIN to TMAX		16	
Turn-Off Time (Note 6)	tOFF	VNO_, VNC_ = 3V; RL = 300Ω, CL = 35pF, Figure 1a	TA = +25°C	5	6	ns
			TA = TMIN to TMAX		8	
Break-Before-Make Time (Note 6)	tBBM	VNO_, VNC_ = 3V; RL = 300Ω, CL = 35pF, Figure 1b	TA = +25°C	7		ns
			TA = TMIN to TMAX	1		
Charge Injection	Q	VGEN = 2V, RGEN = 0, CL = 1.0nF, Figure 2		2		pC
NO_, NC_ Off-Capacitance	CNO_(OFF), CNC_(OFF)	VNO_, VNC_ = GND, f = 1MHz, Figure 3		9		pF
COM_ On-Capacitance	CCOM_(ON)	VCOM_ = GND, f = 1MHz, Figure 3		32		pF
Off-Isolation (Note 7)	VISO	CL = 5pF, RL = 50Ω, f = 10MHz, Figure 4		-52		dB
		CL = 5pF, RL = 50Ω, f = 1MHz, Figure 4		-65		
Crosstalk (Note 8)	VCT	CL = 5pF, RL = 50Ω, f = 10MHz, Figure 4		-66		dB
		CL = 5pF, RL = 50Ω, f = 1MHz, Figure 4		-67		
Total Harmonic Distortion	THD	RL = 600Ω, VNO_ = 5Vp-p, f = 20Hz to 20kHz		0.1		%
SUPPLY						
Positive Supply Current	I+	V+ = 5.5V, VIN_ = 0 or V+		0.001	1.0	μA

ELECTRICAL CHARACTERISTICS—Single +3V Supply

(V+ = +2.7V to +3.6V, VIH = +2.0V, VIL = +0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at TA = +25°C.) (Notes 2, 9)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
ANALOG SWITCH							
Analog Signal Range	VCOM_, VNO_, VNC_		0		V+	V	
On-Resistance	RON	V+ = 2.7V, ICOM_ = 10mA, VNO_ or VNC_ = 0 to V+	TA = +25°C	5	5.5	Ω	
			TA = TMIN to TMAX		8		
On-Resistance Match Between Channels (Notes 3, 4)	ΔRON	V+ = 2.7V, ICOM_ = 10mA, VNO_ or VNC_ = 0 to V+	TA = +25°C	0.1	0.2	Ω	
			TA = TMIN to TMAX		0.4		
On-Resistance Flatness (Note 5)	RFLAT(ON)	V+ = 2.7V, ICOM_ = 10mA, VNO_ or VNC_ = 0 to V+	TA = +25°C	1.5	2	Ω	
			TA = TMIN to TMAX		2.5		
NO_, NC_ Off-Leakage Current (Note 6)	INO_(OFF), INC_(OFF)	V+ = 3.3V; VCOM_ = 1V, 3V; VNO_ or VNC_ = 3V, 1V	TA = +25°C	-0.1	±0.01	0.1	nA
			TA = TMIN to TMAX	-0.3		0.3	
COM_ Off-Leakage Current (Note 6)	ICOM_(OFF)	V+ = 3.3V; VCOM_ = 1V, 3V; VNO_ or VNC_ = 3V, 1V	TA = +25°C	-0.1	±0.01	0.1	nA
			TA = TMIN to TMAX	-0.3		0.3	

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ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)

(V+ = +2.7V to +3.6V, V_{IH} = +2.0V, V_{IL} = +0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.) (Notes 2, 9)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
COM_ On-Leakage Current (Note 6)	I _{COM(ON)}	V+ = 3.3V; V _{COM_} = 1V, 3V; V _{NO_} or V _{NC_} = 1V, 3V, or floating	T _A = +25°C	-0.1	±0.01	0.1	nA
			T _A = T _{MIN} to T _{MAX}	-0.3		0.3	
DIGITAL I/O (IN1, IN2)							
Input Logic High	V _{IH}		2.0			V	
Input Logic Low	V _{IL}				0.4	V	
Input Leakage Current	I _{IH} , I _{IL}	V _{IN_} = 0 or +5.5V	-100	5	100	nA	
DYNAMIC							
Turn-On Time (Note 6)	t _{ON}	V _{NO_} , V _{NC_} = 2V; C _L = 35pF, R _L = 300Ω, Figure 1a	T _A = +25°C	14	18	ns	
			T _A = T _{MIN} to T _{MAX}		20		
Turn-Off Time (Note 6)	t _{OFF}	V _{NO_} , V _{NC_} = 2V; C _L = 35pF, R _L = 300Ω, Figure 1a	T _A = +25°C	6	8	ns	
			T _A = T _{MIN} to T _{MAX}		10		
Break-Before-Make Time (Note 6)		V _{NO_} , V _{NC_} = 2V; C _L = 35pF, R _L = 300Ω, Figure 1b	T _A = +25°C	7		ns	
			T _A = T _{MIN} to T _{MAX}	1			
Charge Injection	Q	V _{GEN} = 1.5V, R _{GEN} = 0, C _L = 1.0nF, Figure 2		11		pC	
NO_, NC_ Off-Capacitance	C _{NO_(OFF)} , C _{NC_(OFF)}	V _{NO_} , V _{NC_} = GND, f = 1MHz, Figure 3		9		pF	
COM On-Capacitance	C _{COM(ON)}	V _{COM} = GND, f = 1MHz, Figure 3		32		pF	
Off-Isolation (Note 7)	V _{ISO}	C _L = 5pF, R _L = 50Ω, f = 10MHz, Figure 4		-52		dB	
		C _L = 5pF, R _L = 50Ω, f = 1MHz, Figure 4		-65			
Crosstalk (Note 8)	V _{CT}	C _L = 5pF, R _L = 50Ω, f = 10MHz, Figure 4		-66		dB	
		C _L = 5pF, R _L = 50Ω, f = 1MHz, Figure 4		-67			
SUPPLY							
Positive Supply Current	I+	V+ = 3.6V, V _{IN} = 0 or +3.6V		0.001	1	μA	

Note 2: The algebraic convention, where the most negative value is a minimum and the most positive value a maximum, is used in this data sheet.

Note 3: $\Delta R_{ON} = R_{ON(MAX)} - R_{ON(MIN)}$.

Note 4: ΔR_{ON} matching specifications for QFN-packaged parts are guaranteed by design.

Note 5: Flatness is defined as the difference between the maximum and minimum values of on-resistance as measured over the specified analog signal ranges.

Note 6: Guaranteed by design.

Note 7: Off-Isolation = $20 \log_{10} (V_{COM} / V_{NO})$, V_{COM} = output, V_{NO} = input to off switch.

Note 8: Between any two switches.

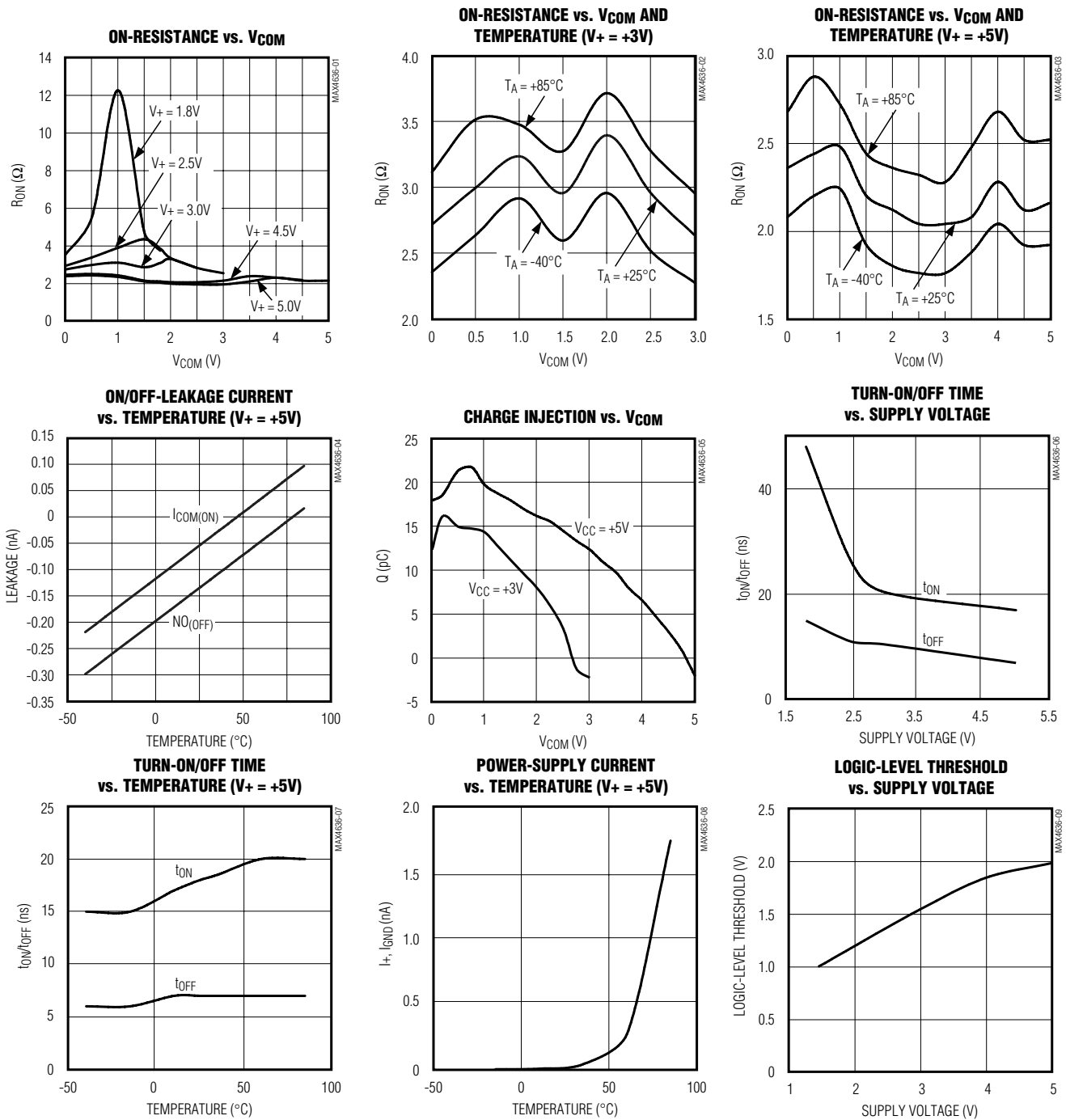
Note 9: QFN packaged parts are tested at +25°C and guaranteed by design and correlation over the entire temperature range.

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Typical Operating Characteristics

($T_A = +25^\circ\text{C}$, unless otherwise noted.)

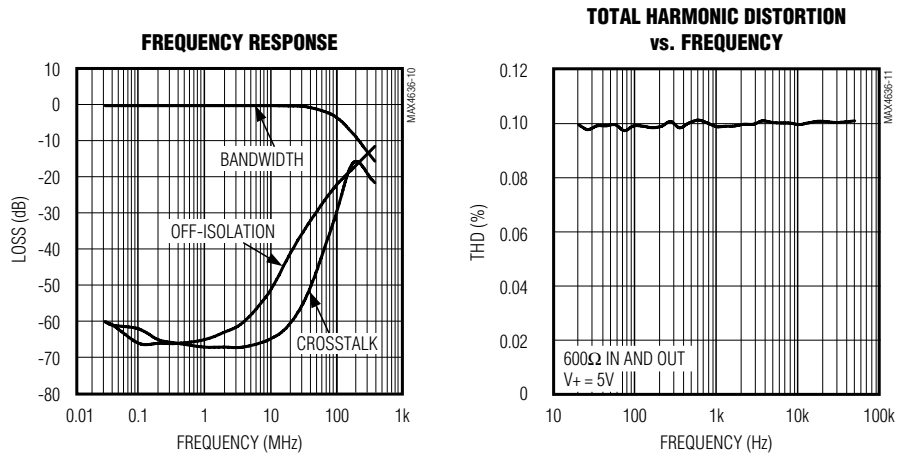
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Typical Operating Characteristics (continued)

(T_A = +25°C, unless otherwise noted.)



Pin Description

PIN		NAME	FUNCTION
MAX4635	MAX4636		
1	1	IN1	Logic Control for Switch 1
2	9	NO1	Normally Open Terminal of Switch 1
3	3	GND	Ground
4	7	NO2	Normally Open Terminal of Switch 2
5	5	IN2	Logic Control Input for Switch 2
6	6	COM2	Common Terminal of Switch 2
7	4	NC2	Normally Closed Terminal of Switch 2
8	8	V+	Input Supply Voltage, +1.8V to +5.5V
9	2	NC1	Normally Closed Terminal of Switch 1
10	10	COM1	Common Terminal of Switch 1

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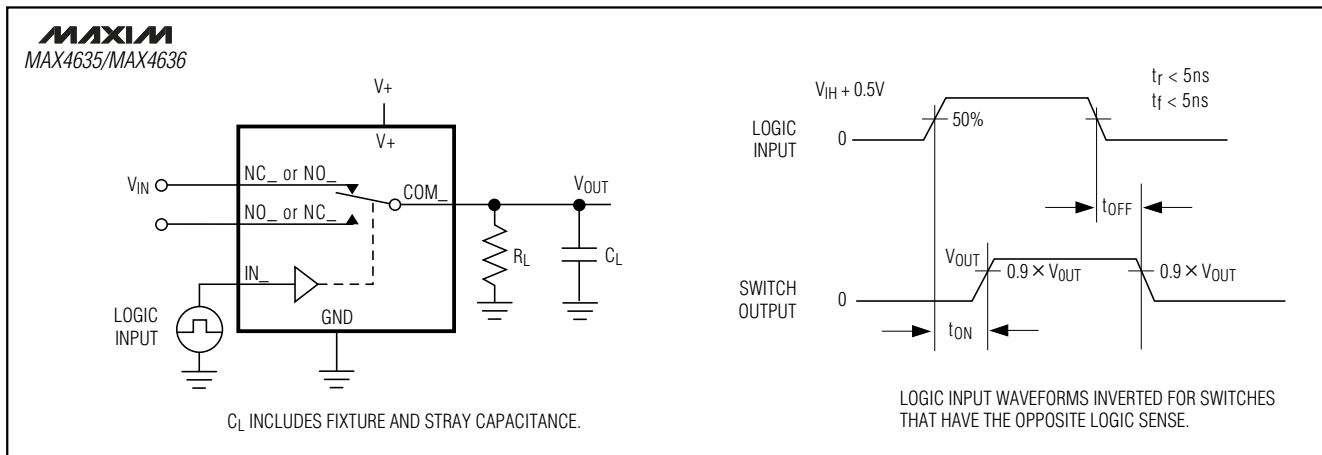


Figure 1a. Switching Time

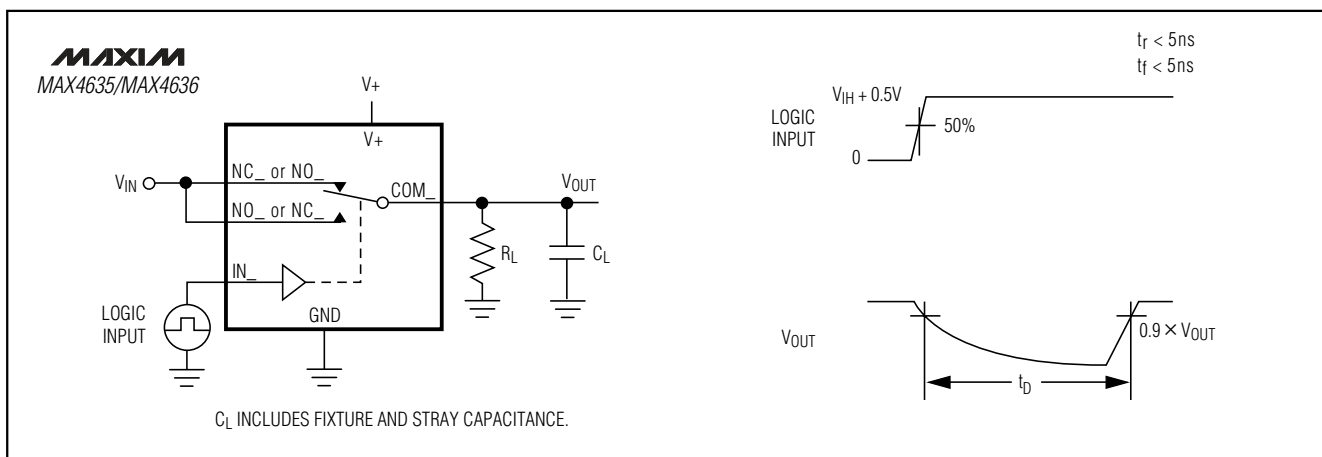


Figure 1b. Break-Before-Make Interval

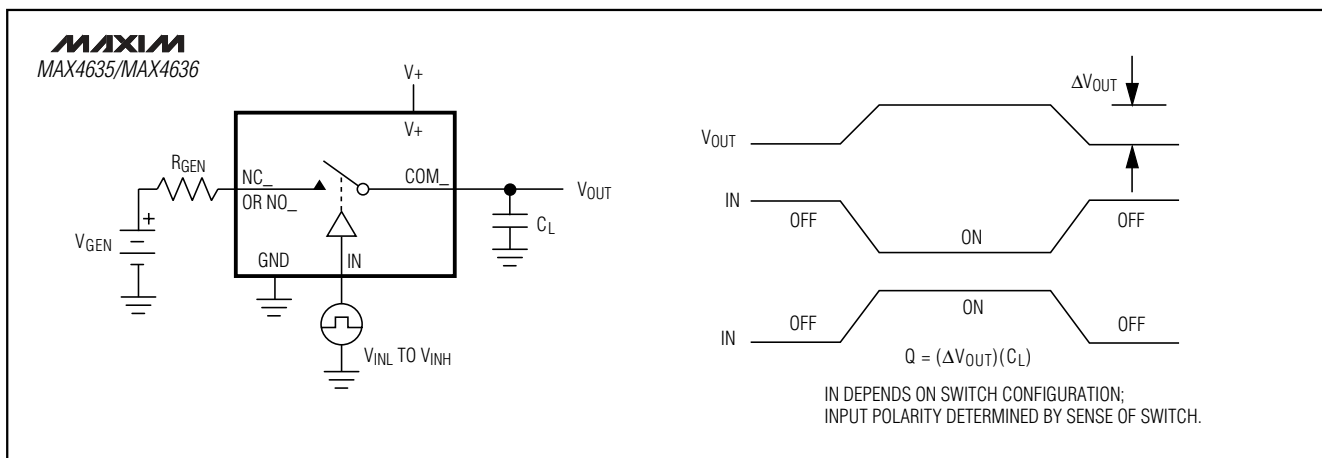


Figure 2. Charge Injection

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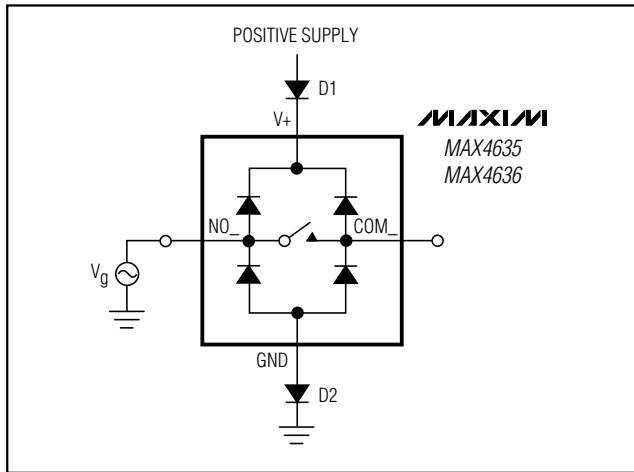


Figure 5. Overvoltage Protection Using Two External Blocking Diodes

On-resistance increases slightly at low supply voltages. Maximum supply voltage (V+) must not exceed +6V. Adding protection diode D2 causes the logic threshold to be shifted relative to GND. Protection diodes D1 and D2 also protect against some overvoltage situations. With Figure 5's circuit, if the supply voltage is below the absolute maximum rating, and if a fault voltage up to the absolute maximum rating is applied to an analog signal pin, no damage results.

Chip Information

TRANSISTOR COUNT: 239

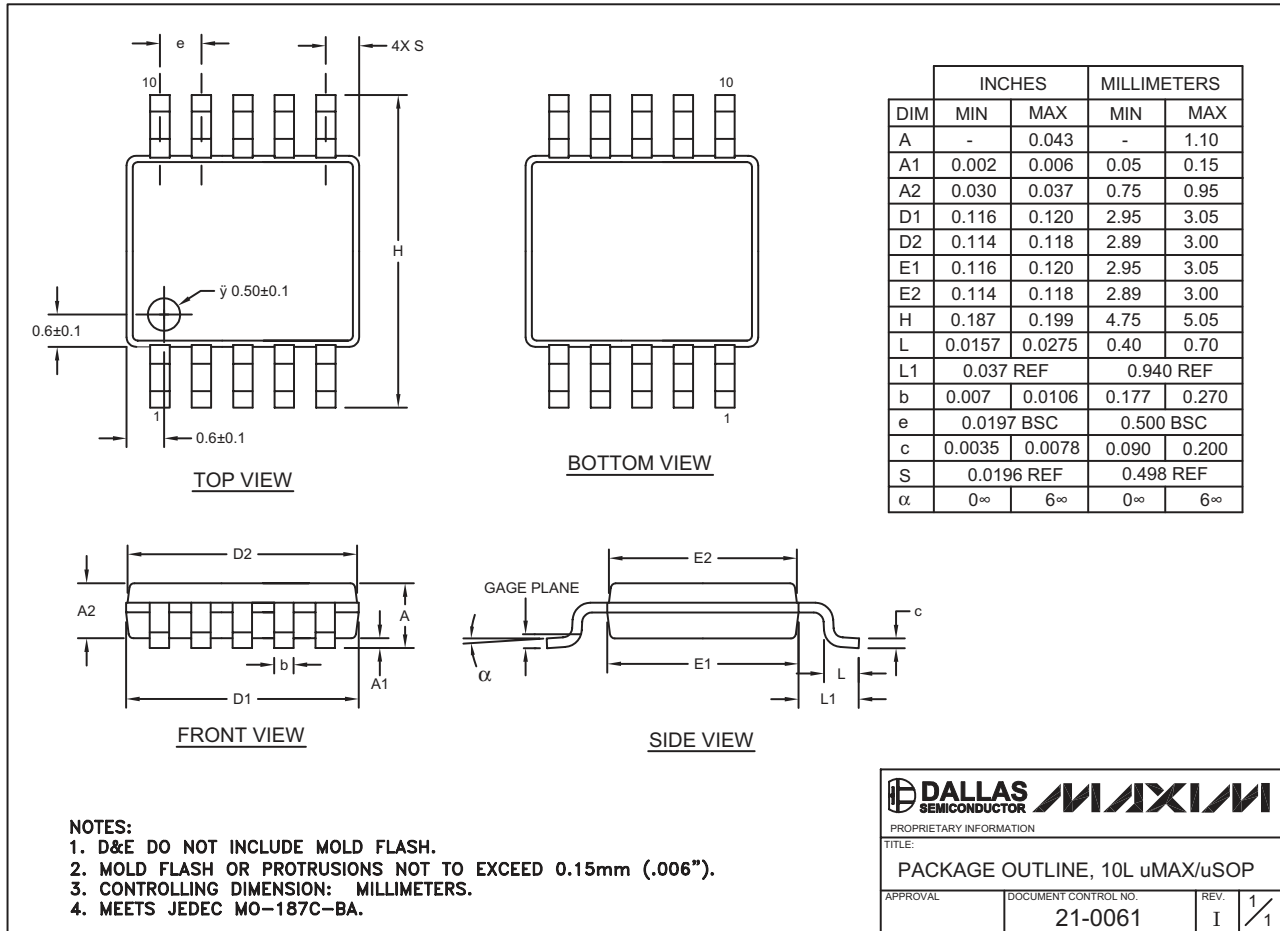
PROCESS: CMOS

MAX4635/MAX4636

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Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



10LUMAXEPS

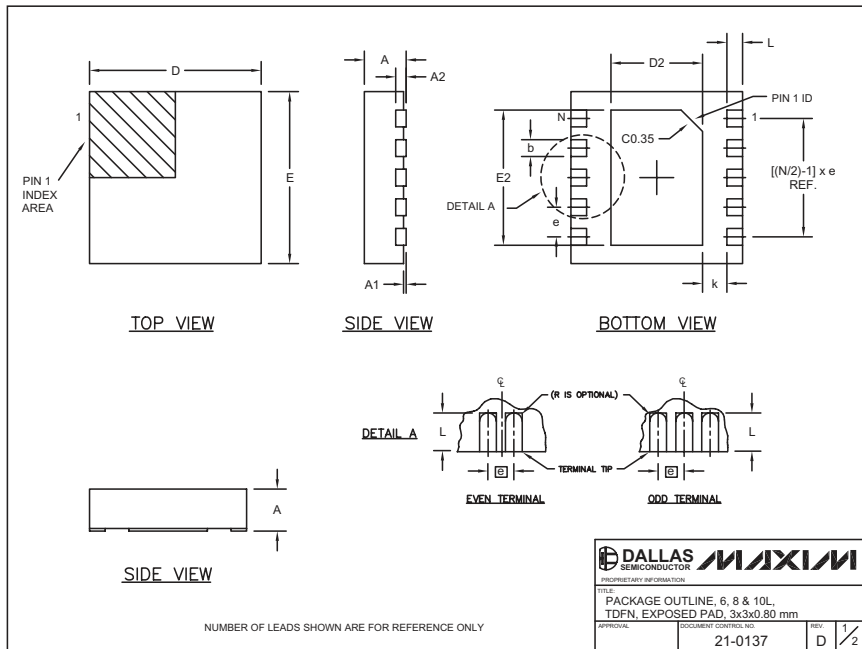
Note: The MAX4636 does not have an exposed pad.

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Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)

MAX4635/MAX4636



COMMON DIMENSIONS							
SYMBOL	MIN.	MAX.					
A	0.70	0.80					
D	2.90	3.10					
E	2.90	3.10					
A1	0.00	0.05					
L	0.20	0.40					
k	0.25 MIN.						
A2	0.20 REF.						

PACKAGE VARIATIONS							
PKG. CODE	N	D2	E2	e	JEDEC SPEC	b	[(N/2)-1] x e
T633-1	6	1.50±0.10	2.30±0.10	0.95 BSC	MO229 / WEEA	0.40±0.05	1.90 REF
T833-1	8	1.50±0.10	2.30±0.10	0.65 BSC	MO229 / WEEC	0.30±0.05	1.95 REF
T1033-1	10	1.50±0.10	2.30±0.10	0.50 BSC	MO229 / WEED-3	0.25±0.05	2.00 REF

NOTES:

1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY SHALL NOT EXCEED 0.08 mm.
3. WARPAGE SHALL NOT EXCEED 0.10 mm.
4. PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC(S).
5. DRAWING CONFORMS TO JEDEC MO229, EXCEPT DIMENSIONS "D2" AND "E2".
6. "N" IS THE TOTAL NUMBER OF LEADS.

DALLAS SEMICONDUCTOR		MAXIM	
<small>PROPRIETARY INFORMATION</small>			
TITLE: PACKAGE OUTLINE, 6, 8 & 10L, TDFN, EXPOSED PAD, 3x3x0.80 mm			
<small>APPROVAL</small>	<small>DOCUMENT CONTROL NO.</small>	<small>REV.</small>	<small>2/2</small>
	21-0137	D	2/2

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